

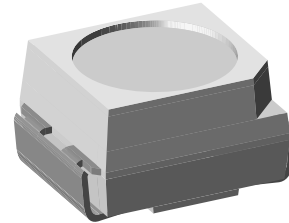
High Intensity SMD LED

Description

This device has been designed to meet the increasing demand for AlInGaP technology.

The package of the TLME310. is the PLCC-2 (equivalent to a size B tantalum capacitor).

It consists of a lead frame which is embedded in a white thermoplast. The reflector inside this package is filled up with clear epoxy.



94 8553

Features

- SMD LED with exceptional brightness
- Luminous intensity categorized
- Compatible with automatic placement equipment
- EIA and ICE standard package
- Compatible with infrared, vapor phase and wave solder processes according to CECC
- Available in 8 mm tape
- Low profile package
- Non-diffused lens: excellent for coupling to light pipes and backlighting
- Low power consumption
- Luminous intensity ratio in one packaging unit
 $I_{Vmax}/I_{Vmin} \leq 1.6$
- Lead-free device

Applications

Automotive: Backlighting in dashboards and switches

Telecommunication: Indicator and backlighting in telephone and fax

Indicator and backlight for audio and video equipment

Indicator and backlight in office equipment

Flat backlight for LCDs, switches and symbols

General use

Parts Table

Part	Color, Luminous Intensity	Angle of Half Intensity ($\pm\phi$)	Technology
TLME3100	Yellow, $I_V > 25$ mcd	60 °	AlInGaP on GaAs
TLME3101	Yellow, $I_V = (32 \text{ to } 100)$ mcd	60 °	AlInGaP on GaAs
TLME3105	Yellow, $I_V = (50 \text{ to } 160)$ mcd	60 °	AlInGaP on GaAs

Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

TLME310.

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
DC Forward current	$T_{amb} \leq 60^\circ\text{C}$	I_F	30	mA
Surge forward current	$t_p \leq 10 \mu\text{s}$	I_{FSM}	0.1	A
Power dissipation	$T_{amb} \leq 60^\circ\text{C}$	P_V	80	mW

Parameter	Test condition	Symbol	Value	Unit
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 55 to + 100	°C
Soldering temperature	$t \leq 5$ s	T_{sd}	260	°C
Thermal resistance junction/ambient	mounted on PC board (pad size > 16 mm ²)	R_{thJA}	400	K/W

Optical and Electrical Characteristics

$T_{amb} = 25$ °C, unless otherwise specified

Yellow

TLME310.

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity	$I_F = 10$ mA	TLME3100	I_V	25	50		mcd
		TLME3101	I_V	32		100	mcd
		TLME3105	I_V	50		160	mcd
Dominant wavelength	$I_F = 10$ mA		λ_d	581	588	594	nm
Peak wavelength	$I_F = 10$ mA		λ_p		590		nm
Angle of half intensity	$I_F = 10$ mA		ϕ		± 60		deg
Forward voltage	$I_F = 20$ mA		V_F		2	2.6	V
Reverse voltage	$I_R = 10$ μ A		V_R	5			V
Junction capacitance	$V_R = 0$, $f = 1$ MHz		C_j		15		pF

in one Packing Unit $I_{Vmax}/I_{Vmin} \leq 1.6$

Typical Characteristics ($T_{amb} = 25$ °C unless otherwise specified)

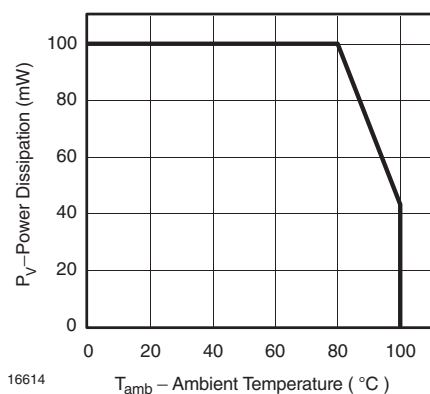


Figure 1. Power Dissipation vs. Ambient Temperature

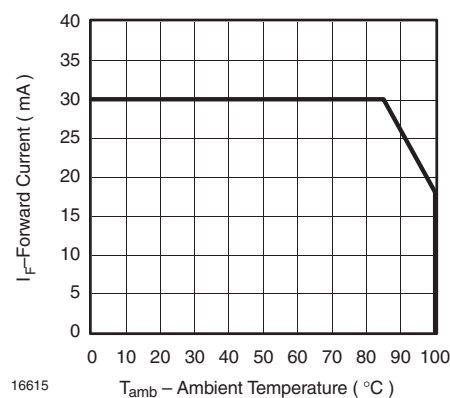
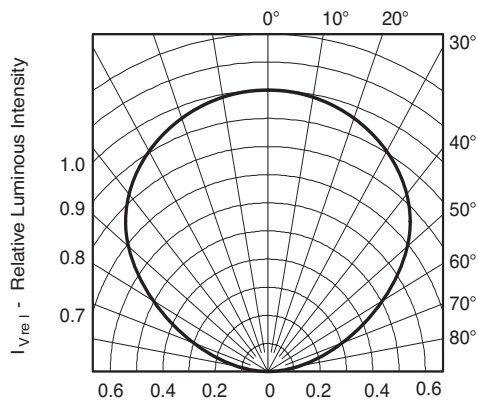
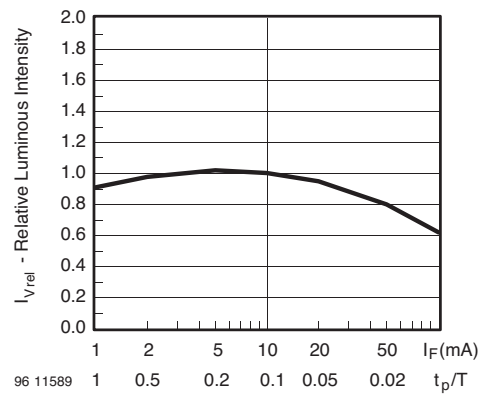


Figure 2. Forward Current vs. Ambient Temperature for InGaN



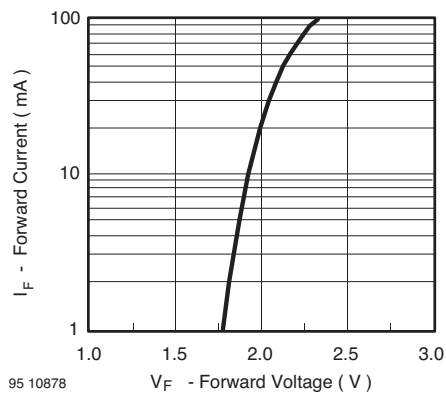
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Figure 3. Rel. Luminous Intensity vs. Angular Displacement



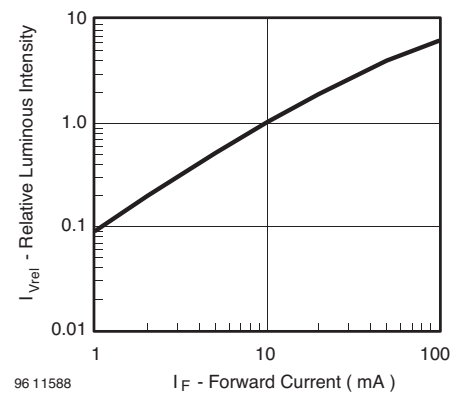
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Figure 6. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle



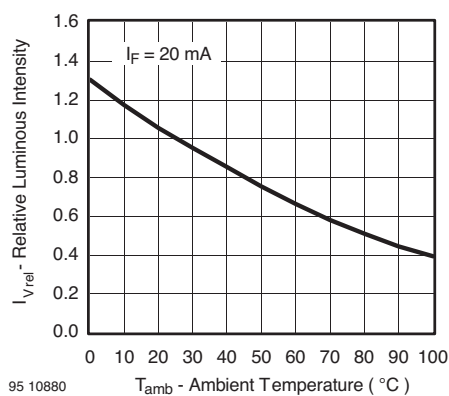
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Figure 4. Forward Current vs. Forward Voltage



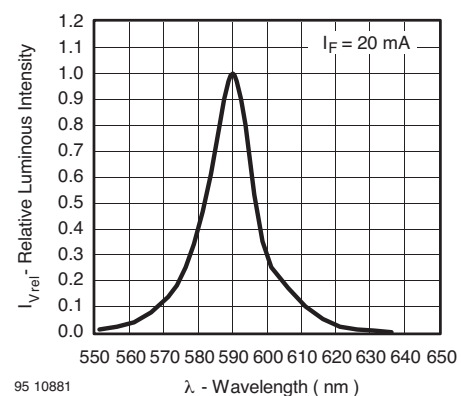
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Figure 7. Relative Luminous Intensity vs. Forward Current



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Figure 5. Rel. Luminous Intensity vs. Ambient Temperature



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Figure 8. Relative Intensity vs. Wavelength

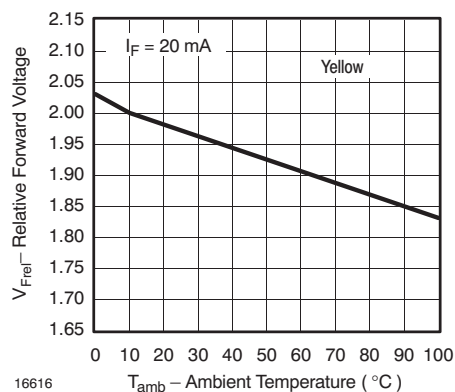


Figure 9. Forward Voltage vs. Ambient Temperature

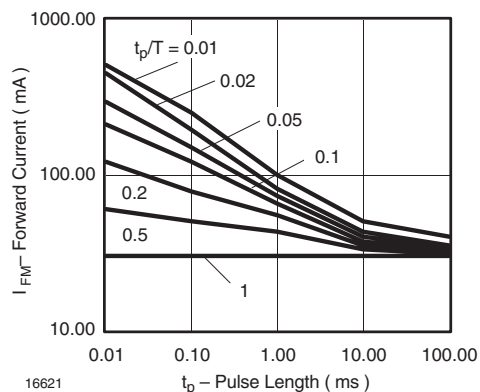
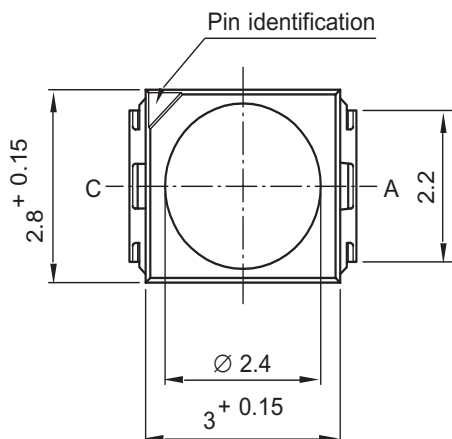
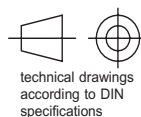
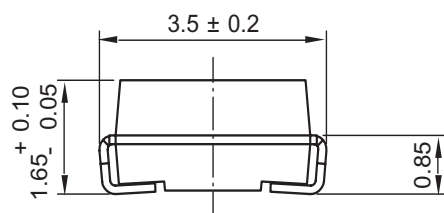


Figure 10. Forward Current vs. Pulse Length

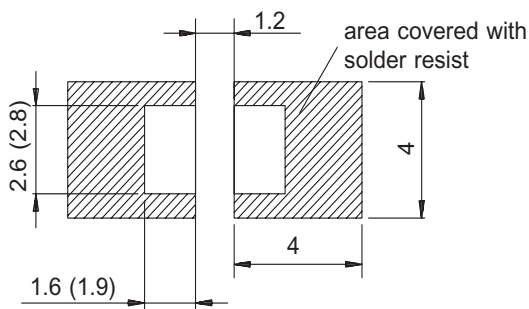
Package Dimensions in mm



Drawing-No. : 6.541-5025.01-4
Issue: 7; 05.04.04

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Mounting Pad Layout



Dimensions: IR and Vaporphase
(Wave Soldering)

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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